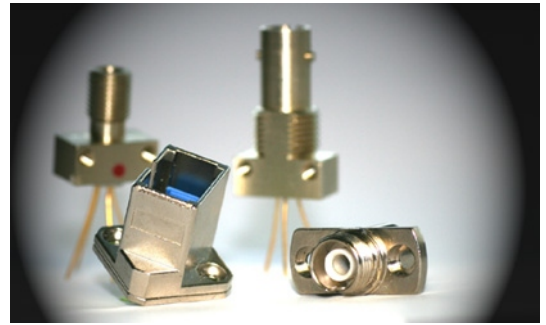


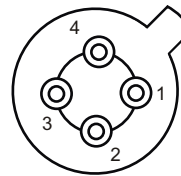
Silicon Photodetector 1.25 Gbps with TIA and AGC

Features of Diode

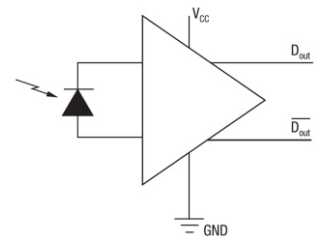
- Silicon Photodetector / Low Noise Transimpedance Amplifier
- Large Active Area of 250 μm
- High Bandwidth/ Wide Dynamic Range
- Automatic Gain Control (AGC)
- Hermetically Sealed TO-46 Can
- Single 3.3 V to 5 V Power Supply
- Differential Output



PINOUT



Bottom view



Functional Schematic

Absolute maximum ratings

Parameter	Min.	Max.
Storage temperature	-55 °C	125 °C
Operating temperature	-40 °C	75 °C
Supply voltage	0 V	6 V

Number	Function
1	D _{out}
2	V _{CC}
3	$\overline{\text{D}}_{\text{out}}$
4	GND

Electrical-optical characteristics

Parameter Laser Diode	Test Condition	Min.	Typ.	Max.
Power supply	T _A = 23 °C, V _{CC} = 5.0 V, 850 nm	3.0 V		5.5 V
Differential output voltage	T _A = 23 °C, V _{CC} = 5.0 V, 850 nm		200 mV	
Supply current	T _A = 23 °C, V _{CC} = 5.0 V, 850 nm		38 mA	50 mA
Detection range			850 nm	
Responsivity	-19 dBm, differential		3000 V/W	
Bandwidth	- 3 dB, small signal	800 MHz	1000 MHz	
Saturation power		-3 dBm	0 dBm	
Sensitivity	BER = 10 ⁻¹⁰ , PRBS ²⁷ -1	-20 dBm	-23 dBm	
Output resistance		40	50	62
Possible receptacle (type A)	ST1, ST2, ST4, P2, LC, SC, FC1, FC2, Fiberdip, SMA1, SMA2			

Compliant with RoHS-requirements (2002/95/EG vom 27.01.2003)

Note: The above product specifications are subject to change without notice.